

Yasuaki Ishikawa

List of Publications by Year in descending order

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204
papers

1,854
citations

331259

21
h-index

414034

32
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all docs

207
docs citations

207
times ranked

2305
citing authors

#	ARTICLE	IF	CITATIONS
1	Evaluation of annual performance for building-integrated photovoltaics based on 2-terminal perovskite/silicon tandem cells under realistic conditions. <i>Energy Science and Engineering</i> , 2022, 10, 1373-1383.	1.9	2
2	Recover possibilities of potential induced degradation caused by the micro-cracked locations in p-type crystalline silicon solar cells. <i>Progress in Photovoltaics: Research and Applications</i> , 2021, 29, 423-432.	4.4	10
3	Improvement in 4-terminal perovskite/silicon heterojunction tandem solar cells™ performance with an index matching layer of silicon nitride. , 2021, , .		0
4	Impact of Mg level on lattice relaxation in a p-AlGaIn hole source layer and attempting excimer laser annealing on p-AlGaIn HSL of UVB emitters. <i>Nanotechnology</i> , 2021, 32, 055702.	1.3	23
5	Optical and Electrical Transport Evaluations of n-Type Iron Pyrite Single Crystals. <i>ACS Omega</i> , 2021, 6, 31358-31365.	1.6	2
6	Rapid photo-assisted activation and enhancement of solution-processed InZnO thin-film transistors. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 045102.	1.3	5
7	Evaluate Fixed Charge and Oxide-Trapped Charge on SiO ₂ /GaIn Metal-Oxide-Semiconductor Structure Before and After Postannealing. <i>Physica Status Solidi (B): Basic Research</i> , 2020, 257, 1900444.	0.7	8
8	P&C1: High Performance All-Solution Processed InZnO Thin-Film Transistors via Photo-Functionalization at Varying Fluence and Annealing Environment. <i>Digest of Technical Papers SID International Symposium</i> , 2020, 51, 1350-1353.	0.1	1
9	Enhanced Thermoelectric Transport and Stability in Atomic Layer Deposited-HfO ₂ /ZnO and TiO ₂ /ZnO-Sandwiched Multilayer Thin Films. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 49210-49218.	4.0	16
10	High-Performance Fully Solution-Processed Oxide Thin-Film Transistors via Photo-Assisted Role Tuning of InZnO. <i>ACS Applied Electronic Materials</i> , 2020, 2, 2398-2407.	2.0	17
11	Improvement in Bias Stress Stability of Solution-Processed Amorphous InZnO Thin-Film Transistors via Low-Temperature Photosensitive Passivation. <i>IEEE Electron Device Letters</i> , 2020, 41, 1372-1375.	2.2	12
12	Hierarchical core-shell heterostructure of H ₂ O-oxidized ZnO nanorod@Mg-doped ZnO nanoparticle for solar cell applications. <i>Materials Advances</i> , 2020, 1, 1253-1261.	2.6	15
13	7&C2: Invited Paper: Hot Carrier Degradation in High Mobility Metal Oxide Thin Film Transistors. <i>Digest of Technical Papers SID International Symposium</i> , 2020, 51, 71-74.	0.1	0
14	Optimizing the thermoelectric performance of InGaZnO thin films depending on crystallinity via hydrogen incorporation. <i>Applied Surface Science</i> , 2020, 527, 146791.	3.1	11
15	Development of High-Reliability and -Stability Chemical Sensors Based on an Extended-Gate Type Amorphous Oxide Semiconductor Thin-Film Transistor. <i>ACS Applied Electronic Materials</i> , 2020, 2, 405-408.	2.0	8
16	Influence of shadow on shunt-type potential-induced degradation for crystalline Si photovoltaic modules exposed outdoors. <i>Japanese Journal of Applied Physics</i> , 2020, 59, SGGF04.	0.8	0
17	Elucidating the mechanism of potential induced degradation delay effect by ultraviolet light irradiation for p-type crystalline silicon solar cells. <i>Solar Energy</i> , 2020, 199, 55-62.	2.9	15
18	Bias stress and humidity exposure of amorphous InGaZnO thin-film transistors with atomic layer deposited Al ₂ O ₃ passivation using dimethylaluminum hydride at 200 Å°C. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 165103.	1.3	6

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19	Optoelectronic properties of electron beam-deposited NiOx thin films for solar cell application. Results in Physics, 2020, 17, 103122.	2.0	26
20	Unique degradation under AC stress in high-mobility amorphous In ^W Zn ^O thin-film transistors. Applied Physics Express, 2020, 13, 054003.	1.1	13
21	Extension of the {100}-Oriented Grain-Boundary Free Si Thin Film Grown by a Continuous-Wave Laser Lateral Crystallization. Thin Solid Films, 2020, 708, 138127.	0.8	7
22	High Performance Amorphous In ^{Ga} Zn ^O Thin-Film Transistors with Low Temperature High-k Solution Processed Hybrid Gate Insulator. ECS Journal of Solid State Science and Technology, 2020, 9, 025002.	0.9	5
23	Air-stable perovskite photovoltaic cells with low temperature deposited NiOx as an efficient hole-transporting material. Optical Materials Express, 2020, 10, 1801.	1.6	19
24	Relationship of phase shift mask design and size of three-dimension nanostructures. , 2020, , .		0
25	Photo-assisted Processing of Amorphous Gallium Oxide (a-GaOx) Thin Film for Flexible and Transparent Device Application. , 2020, , .		1
26	Removing process of the three-dimension periodic nanostructure fabricated from KMPR photoresist. Japanese Journal of Applied Physics, 2019, 58, SDDF08.	0.8	1
27	Hot carrier effects in InGaZnO thin-film transistor. Applied Physics Express, 2019, 12, 094007.	1.1	21
28	Effective minority carrier lifetime as an indicator for potential-induced degradation in p-type single-crystalline silicon photovoltaic modules. Japanese Journal of Applied Physics, 2019, 58, 106507.	0.8	4
29	Low Temperature High-k Solution Processed Hybrid Gate Insulator for High Performance Amorphous In-Ga-Zn-O Thin-Film Transistors. , 2019, , .		1
30	High Performance All Solution Processed Oxide Thin-Film Transistor via Photo-induced Semiconductor-to-Conductor Transformation of a-InZnO. Digest of Technical Papers SID International Symposium, 2019, 50, 422-425.	0.1	7
31	193: Late News Poster: Low Temperature Solution Processed InZnO TFT Annealed in Wet Ambient. Digest of Technical Papers SID International Symposium, 2019, 50, 1333-1336.	0.1	0
32	Transient carrier recombination dynamics in potential-induced degradation p-type single-crystalline Si photovoltaic modules. Progress in Photovoltaics: Research and Applications, 2019, 27, 682-692.	4.4	2
33	Highly reliable low-temperature (180 °C) solution-processed passivation for amorphous In ^{Zn} O thin-film transistors. Applied Physics Express, 2019, 12, 064002.	1.1	8
34	Degradation phenomenon in metal-oxide-semiconductor thin-film transistors and techniques for its reliability evaluation and suppression. Japanese Journal of Applied Physics, 2019, 58, 090502.	0.8	9
35	Improvement of the stability of an electric double-layer transistor using a 1H,1H,2H,2H-perfluorodecyltriethoxysilane barrier layer. Japanese Journal of Applied Physics, 2019, 58, 040907.	0.8	1
36	Physical and electrical properties of ALD-Al ₂ O ₃ /GaN MOS capacitor annealed with high pressure water vapor. Japanese Journal of Applied Physics, 2019, 58, 040902.	0.8	4

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37	Influence of UV light on the increase of SiNx conductivity toward elucidation of potential induced degradation mechanism. , 2019, , .		1
38	Segregation-free bromine-doped perovskite solar cells for IoT applications. RSC Advances, 2019, 9, 32833-32838.	1.7	13
39	The optical properties of silicon-rich silicon nitride prepared by plasma-enhanced chemical vapor deposition. Materials Science in Semiconductor Processing, 2019, 90, 54-58.	1.9	7
40	Improvement of Amorphous InGaZnO Thin-Film Transistor Using High-k SrTa ₂ O ₆ as Gate Insulator Deposited by Sputtering Method. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1700773.	0.8	3
41	Growth and characterization of low composition Ge, x in epi-Si _{1-x} Ge _x (x = 0.1/2, 0.10%) active layer for fabrication of hydrogenated bottom solar cell. Journal Physics D: Applied Physics, 2018, 51, 185107.		5
42	Fluorine incorporation in solution-processed poly-siloxane passivation for highly reliable InGaZnO thin-film transistors. Journal Physics D: Applied Physics, 2018, 51, 125105.	1.3	11
43	Effect of inversion layer at iron pyrite surface on photovoltaic device. Japanese Journal of Applied Physics, 2018, 57, 032301.	0.8	9
44	Alterations in ambipolar characteristic of graphene due to adsorption of Escherichia colibacteria. Journal Physics D: Applied Physics, 2018, 51, 115102.	1.3	3
45	Structural study of NiOx thin films fabricated by radio frequency sputtering at low temperature. Thin Solid Films, 2018, 646, 209-215.	0.8	9
46	Carrier dynamics in the potential-induced degradation in single-crystalline silicon photovoltaic modules. Japanese Journal of Applied Physics, 2018, 57, 08RG14.	0.8	6
47	One-dimensional array of gold nanoparticles fabricated using biotemplate and its application to fine FET. Japanese Journal of Applied Physics, 2018, 57, 06HC05.	0.8	2
48	Ultrashort intrinsic-like channel FETs with nanodot-type floating gate utilizing biomaterial. Japanese Journal of Applied Physics, 2018, 57, 125003.	0.8	0
49	Influence of carbon impurities and oxygen vacancies in Al ₂ O ₃ film on Al ₂ O ₃ /GaN MOS capacitor characteristics. AIP Advances, 2018, 8, .	0.6	26
50	Dimethylaluminum hydride for atomic layer deposition of Al ₂ O ₃ passivation for amorphous InGaZnO thin-film transistors. Applied Physics Express, 2018, 11, 061103.	1.1	11
51	High performance top gate a-IGZO TFT utilizing siloxane hybrid material as a gate insulator. AIP Advances, 2018, 8, .	0.6	13
52	SrTa ₂ O ₆ induced low voltage operation of InGaZnO thin-film transistors. Thin Solid Films, 2018, 665, 173-178.	0.8	4
53	Reliability Enhancement of Solution Processed Amorphous In-Zn-O Thin-Film Transistors via a Low Temperature (180 Å°C) Solution Processed Passivation. , 2018, , .		0
54	The influence of sodium ions decorated micro-cracks on the evolution of potential induced degradation in p-type crystalline silicon solar cells. Solar Energy, 2018, 174, 1-6.	2.9	25

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55	Low temperature cured poly-siloxane passivation for highly reliable <i>a</i> -InGaZnO thin-film transistors. Applied Physics Letters, 2018, 112, .	1.5	18
56	Instantaneous Semiconductor-to-Conductor Transformation of a Transparent Oxide Semiconductor <i>a</i> -InGaZnO at 45 Å°C. ACS Applied Materials & Interfaces, 2018, 10, 24590-24597.	4.0	12
57	Self-Heating Suppressed Structure of <i>a</i> -IGZO Thin-Film Transistor. IEEE Electron Device Letters, 2018, 39, 1322-1325.	2.2	9
58	Significant mobility improvement of amorphous In-Ga-Zn-O thin-film transistors annealed in a low temperature wet ambient environment. Applied Physics Letters, 2018, 112, 193501.	1.5	20
59	Photosensitive polysiloxane passivation fabricated at low temperature for highly reliable amorphous InGaZnO thin-film transistors. Japanese Journal of Applied Physics, 2018, 57, 090306.	0.8	2
60	Properties of TlZnSnO film fabricated via sputtering from TlZnSnO target. Journal Physics D: Applied Physics, 2018, 51, 415103.	1.3	0
61	Easy and green preparation of a grapheneâ€TiO ₂ nanohybrid using a supramolecular biomaterial consisting of artificially bifunctionalized proteins and its application for a perovskite solar cell. Nanoscale, 2018, 10, 19249-19253.	2.8	6
62	Numerical analysis of monocrystalline silicon solar cells with fine nanoimprinted textured surface. Japanese Journal of Applied Physics, 2017, 56, 022301.	0.8	4
63	Photomechanical modification of ZnS microcrystal to enhance electroluminescence by ultrashort-pulse laser processing. Applied Physics Express, 2017, 10, 021201.	1.1	3
64	H and Au diffusion in high mobility <i>a</i> -InGaZnO thin-film transistors via low temperature KrF excimer laser annealing. Applied Physics Letters, 2017, 110, .	1.5	14
65	Low surface reflectance by nanoimprinted texture with silicon-rich silicon nitride layer. Journal Physics D: Applied Physics, 2017, 50, 455108.	1.3	2
66	Fabrication of perovskite solar cells using sputter-processed CH ₃ NH ₃ PbI ₃ films. Applied Physics Express, 2017, 10, 094101.	1.1	19
67	Biotemplated Synthesis of TiO ₂ -Coated Gold Nanowire for Perovskite Solar Cells. ACS Omega, 2017, 2, 5478-5485.	1.6	6
68	Growth of InGaZnO nanowires via a Mo/Au catalyst from amorphous thin film. Applied Physics Letters, 2017, 111, 033104.	1.5	4
69	Solution-derived SiO ₂ gate insulator formed by CO ₂ laser annealing for polycrystalline silicon thin-film transistors. Japanese Journal of Applied Physics, 2017, 56, 056503.	0.8	3
70	Fabrication of Nanoshell-Based 3D Periodic Structures by Templating Process using Solution-derived ZnO. Nanoscale Research Letters, 2017, 12, 419.	3.1	16
71	Estimation of charge effects of ultrafine channel utilizing junctionless transistor with nanodot-type floating gate. Japanese Journal of Applied Physics, 2017, 56, 03BB05.	0.8	0
72	Effect of Gold Nanoparticle Distribution in TiO ₂ on the Optical and Electrical Characteristics of Dye-Sensitized Solar Cells. Nanoscale Research Letters, 2017, 12, 513.	3.1	27

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73	One-dimensional arrangement of nanoparticles utilizing the V-groove and cage shaped proteins. Japanese Journal of Applied Physics, 2017, 56, 06GG11.	0.8	0
74	(Invited) Unseeded Growth of Poly-Crystalline Ge with (111) Surface Orientation on Insulator by Pulsed Green Laser Annealing. ECS Transactions, 2016, 75, 87-94.	0.3	0
75	High-density carrier-accumulated and electrically stable oxide thin-film transistors from ion-gel gate dielectric. Scientific Reports, 2016, 5, 18168.	1.6	24
76	Nano-crystallization in ZnO-doped In ₂ O ₃ thin films via excimer laser annealing for thin-film transistors. AIP Advances, 2016, 6, 065216.	0.6	10
77	Investigation of crystallinity and planar defects in the Si nanowires grown by vapor-liquid-solid mode using indium catalyst for solar cell applications. Japanese Journal of Applied Physics, 2016, 55, 01AE03.	0.8	7
78	Self-heating induced instability of oxide thin film transistors under dynamic stress. Applied Physics Letters, 2016, 108, .	1.5	7
79	Localized defect study of laboratory PID tested module. , 2016, , .		0
80	Effect of Fluorine in a Gate Insulator on the Reliability of Indium-Gallium-Zinc Oxide Thin-Film Transistors. ECS Journal of Solid State Science and Technology, 2016, 5, N17-N21.	0.9	6
81	Selection of a novel peptide aptamer with high affinity for TiO ₂ -nanoparticle through a direct electroporation with TiO ₂ -binding phage complexes. Journal of Bioscience and Bioengineering, 2016, 122, 528-532.	1.1	5
82	Numerical modeling of device structure for FeS ₂ /thin film solar cells. , 2016, , .		0
83	Al ₂ O ₃ /TiO ₂ double layer anti-reflection coating film for crystalline silicon solar cells formed by spray pyrolysis. Energy Science and Engineering, 2016, 4, 269-276.	1.9	36
84	Internal resistance of perovskite solar cells under low illuminance conditions. , 2016, , .		0
85	Characteristics of Perovskite Solar Cells under Low-Illuminance Conditions. Journal of Physical Chemistry C, 2016, 120, 18986-18990.	1.5	43
86	Potential of perovskite solar cells for power sources of IoT applications. , 2016, , .		2
87	Theoretical investigation about the optical characterization of cone-shaped pin-Si nanowire for top cell application. Energy Science and Engineering, 2016, 4, 383-393.	1.9	6
88	Thermoelectric Devices Fabricated Using Amorphous Indium Gallium Zinc Oxide. ECS Transactions, 2016, 75, 213-216.	0.3	0
89	Interface Optoelectronics Engineering for Mechanically Stacked Tandem Solar Cells Based on Perovskite and Silicon. ACS Applied Materials & Interfaces, 2016, 8, 33553-33561.	4.0	36
90	Reactivity and stability of thallium oxide for fabricating TlSnZnO toward thin-film transistors with high mobility. Journal of Alloys and Compounds, 2016, 672, 413-418.	2.8	11

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91	Creating Reversible p-n Junction on Graphene through Ferritin Adsorption. ACS Applied Materials & Interfaces, 2016, 8, 8192-8200.	4.0	12
92	Effect of excimer laser annealing on InGaZnO thin-film transistors passivated by solution-processed hybrid passivation layers. Journal Physics D: Applied Physics, 2016, 49, 035102.	1.3	20
93	Improvement of Thermoelectric Properties of a-InGaZnO Thin Film by Optimizing Carrier Concentration. Journal of Electronic Materials, 2016, 45, 1377-1381.	1.0	7
94	Reliability Improvement of Amorphous InGaZnO Thin-Film Transistors by Less Hydroxyl-Groups Siloxane Passivation. Journal of Display Technology, 2016, 12, 263-267.	1.3	17
95	Biotemplates and Their Application to Electronic Devices. , 2016, , 119-143.		1
96	Crystalline Si solar cells fabricated by CO2 laser doping. , 2015, , .		0
97	Analysis of thermoelectric properties of amorphous InGaZnO thin film by controlling carrier concentration. AIP Advances, 2015, 5, .	0.6	44
98	Highly reliable photosensitive organic-inorganic hybrid passivation layers for InGaZnO thin-film transistors. Applied Physics Letters, 2015, 107, .	1.5	21
99	Comparison between Effects of PECVD-SiO _x and Thermal ALD-AlO _x Passivation Layers on Characteristics of Amorphous InGaZnO TFTs. ECS Journal of Solid State Science and Technology, 2015, 4, Q61-Q65.	0.9	20
100	High-mobility material research for thin-film transistor with amorphous thallium-zinc-tin oxide semiconductor. Japanese Journal of Applied Physics, 2015, 54, 104101.	0.8	2
101	Floating gate memory with charge storage dots array formed by Dps protein modified with site-specific binding peptides. Nanotechnology, 2015, 26, 195201.	1.3	7
102	Unseeded growth of poly-crystalline Ge with (111) surface orientation on insulator by pulsed green laser annealing. , 2015, , .		0
103	On-site detection of defective panels in mega solar systems by handy electroluminescence surveillance. , 2015, , .		0
104	Ultra-short channel junctionless transistor with a one-dimensional nanodot array floating gate. Applied Physics Letters, 2015, 106, .	1.5	7
105	Thermo-stable carbon nanotube-TiO ₂ nanocomposite as electron highways in dye-sensitized solar cell produced by bio-nano-process. Nanotechnology, 2015, 26, 285601.	1.3	11
106	Characteristics of perovskite solar cells under low illuminance condition. , 2015, , .		0
107	Analysis of self-heating phenomenon in oxide thin-film transistors under pulsed bias voltage. , 2015, , .		0
108	Control of verticality and (111) orientation of In-catalyzed silicon nanowires grown in the vapour-liquid-solid mode for nanoscale device applications. Journal of Materials Chemistry C, 2015, 3, 11577-11580.	2.7	10

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109	Evaluation of band structure and conductive property of iron pyrite (FeS ₂) thin film deposited by spin-coating. , 2015, , .		1
110	Thermoelectric properties of a-InGaZnO thin film. , 2015, , .		0
111	Joule heating effect in nonpolar and bipolar resistive random access memory. Applied Physics Letters, 2015, 107, .	1.5	41
112	A distance-controlled nanoparticle array using PEGylated ferritin. Materials Research Express, 2014, 1, 045410.	0.8	3
113	Vapor-Induced Improvements in Field Effect Mobility of Transparent a-IGZO TFTs. ECS Journal of Solid State Science and Technology, 2014, 3, Q3050-Q3053.	0.9	9
114	(Invited) Analysis of Thermal Degradation in Oxide Thin Film Transistors. ECS Transactions, 2014, 64, 71-78.	0.3	0
115	Thermal analysis for observing conductive filaments in amorphous InGaZnO thin film resistive switching memory. Applied Physics Letters, 2014, 105, 123506.	1.5	13
116	Biological Construction of Single-Walled Carbon Nanotube Electron Transfer Pathways in Dye-Sensitized Solar Cells. ChemSusChem, 2014, 7, 2805-2810.	3.6	15
117	Reliability improvement in amorphous InGaZnO thin film transistors passivated by photosensitive polysilsesquioxane passivation layer. , 2014, , .		0
118	The Influence of Fluorinated Silicon Nitride Gate Insulator on Positive Bias Stability toward Highly Reliable Amorphous InGaZnO Thin-Film Transistors. ECS Journal of Solid State Science and Technology, 2014, 3, Q20-Q23.	0.9	29
119	Highly Reliable Polysilsesquioxane Passivation Layer for a-InGaZnO Thin-Film Transistors. ECS Journal of Solid State Science and Technology, 2014, 3, Q16-Q19.	0.9	32
120	Effect of contact material on amorphous InGaZnO thin-film transistor characteristics. Japanese Journal of Applied Physics, 2014, 53, 03CC04.	0.8	30
121	Density of States in Amorphous In-Ga-Zn-O Thin-Film Transistor under Negative Bias Illumination Stress. ECS Journal of Solid State Science and Technology, 2014, 3, Q3001-Q3004.	0.9	34
122	Highly reliable passivation layer for a-InGaZnO thin-film transistors fabricated using polysilsesquioxane. Materials Research Society Symposia Proceedings, 2014, 1633, 139-144.	0.1	6
123	Analysis of printed silver electrode on amorphous indium gallium zinc oxide. Japanese Journal of Applied Physics, 2014, 53, 04EB03.	0.8	12
124	Reliability of bottom gate amorphous InGaZnO thin-film transistors with siloxane passivation layer. , 2014, , .		1
125	Reversible Oxidation of Graphene Through Ultraviolet/Ozone Treatment and Its Nonthermal Reduction through Ultraviolet Irradiation. Journal of Physical Chemistry C, 2014, 118, 27372-27381.	1.5	66
126	Hydrogen behavior from ALD Al ₂ O ₃ passivation layer for amorphous InGaZnO TFTs. , 2014, , .		0

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127	Highly stable dye-sensitized solar cells with quasi-solid-state electrolyte based on Flemion. Solar Energy, 2014, 110, 648-655.	2.9	5
128	Oxidation of graphene film by non-thermal treatment for new sensing devices. , 2014, , .		0
129	Development of solution-derived diffusion barrier layer for back-contact crystalline silicon solar cell. , 2014, , .		1
130	Analysis of heating phenomenon in oxide thin-film transistor under pulse voltage stress. , 2014, , .		0
131	Silica-sol-based spin-coating barrier layer against phosphorous diffusion for crystalline silicon solar cells. Nanoscale Research Letters, 2014, 9, 659.	3.1	6
132	Effects of Si and Ti impurities on electrical properties of sol-gel-derived amorphous SrTa ₂ O ₆ thin films by UV/O ₃ treatment. Applied Physics A: Materials Science and Processing, 2013, 112, 425-430.	1.1	3
133	Crystallization of amorphous Ge thin film using Cu nanoparticle synthesized and delivered by ferritin. Journal of Crystal Growth, 2013, 382, 31-35.	0.7	11
134	Polycrystalline silicon thin-film transistor utilizing self-assembled monolayer for crystallization. Thin Solid Films, 2013, 540, 266-270.	0.8	6
135	Thermal analysis of amorphous oxide thin-film transistor degraded by combination of joule heating and hot carrier effect. Applied Physics Letters, 2013, 102, .	1.5	72
136	Memristive nanoparticles formed using a biotemplate. RSC Advances, 2013, 3, 18044.	1.7	21
137	Thermal reversibility in electrical characteristics of ultraviolet/ozone-treated graphene. Applied Physics Letters, 2013, 103, 063107.	1.5	14
138	Distance controlled nanoparticles using PEG-ferritin for new functional devices. , 2013, , .		0
139	Impact of Underwater Laser Annealing on Polycrystalline Silicon Thin-Film Transistor for Inactivation of Electrical Defects at Super Low Temperature. Journal of Display Technology, 2013, 9, 741-746.	1.3	1
140	Forming of SiO ₂ film by spin-on glass and CO ₂ laser annealing for gate insulator of polycrystalline silicon thin film transistors. , 2013, , .		0
141	Femtosecond laser irradiation to ZnS phosphor for inorganic electroluminescent displays. , 2013, , .		0
142	Effects of Gate Insulator on Thin-Film Transistors With ZnO Channel Layer Deposited by Plasma-Assisted Atomic Layer Deposition. Journal of Display Technology, 2013, 9, 694-698.	1.3	10
143	Numerical analysis of light-trapping structure in nanoimprinted-textured silicon solar cell. , 2013, , .		0
144	Evaluation of TaOx nanoparticles for resistive random access memory. , 2013, , .		0

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145	Fabrication of Zinc Oxide Nanopatterns by Quick Gel-Nanoimprint Process toward Optical Switching Devices. Japanese Journal of Applied Physics, 2013, 52, 03BA02.	0.8	7
146	Plasmon Absorbance of SiO ₂ -Wrapped Gold Nanoparticles Selectively Coupled with Ti Substrate Using Porter Protein. Japanese Journal of Applied Physics, 2013, 52, 125201.	0.8	2
147	Low temperature high-mobility InZnO thin-film transistors fabricated by excimer laser annealing. Applied Physics Letters, 2013, 102, .	1.5	41
148	Analysis of electronic structure of amorphous InGaZnO/SiO ₂ interface by angle-resolved X-ray photoelectron spectroscopy. Journal of Applied Physics, 2013, 114, 163713.	1.1	23
149	Light trapping effect of nanoimprinted-textured crystalline silicon solar cells. , 2013, , .		4
150	Characterizations of Al ₂ O ₃ gate dielectric deposited on n-GaN by plasma-assisted atomic layer deposition. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1426-1429.	0.8	19
151	Thermal distribution in amorphous InSnZnO thin-film transistor. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 1561-1564.	0.8	9
152	Thermally Stimulated Current Analysis of Defects in Sol-Gel Derived SrTa ₂ O ₆ Thin-Film Capacitors. Japanese Journal of Applied Physics, 2012, 51, 09LA18.	0.8	2
153	Thin-Film Devices Fabricated on Double-Layered Polycrystalline Silicon Films Formed by Green Laser Annealing. Japanese Journal of Applied Physics, 2012, 51, 03CA03.	0.8	1
154	Low-Temperature-Processed Zinc Oxide Thin-Film Transistors Fabricated by Plasma-Assisted Atomic Layer Deposition. Japanese Journal of Applied Physics, 2012, 51, 02BF04.	0.8	5
155	Size Control of ZnS Nanoparticles by Electro-Spray Deposition Method. Japanese Journal of Applied Physics, 2012, 51, 03CC02.	0.8	0
156	Low-Operating-Voltage Solution-Processed InZnO Thin-Film Transistors Using High-k SrTa ₂ O ₆ . Japanese Journal of Applied Physics, 2012, 51, 03CB05.	0.8	7
157	Crystallization Using Biomineralized Nickel Nanodots of Amorphous Silicon Thick Films Deposited by Chemical Vapor Deposition, Sputtering and Electron Beam Evaporation. Japanese Journal of Applied Physics, 2012, 51, 03CA01.	0.8	0
158	Guided filament formation in NiO-resistive random access memory by embedding gold nanoparticles. Applied Physics Letters, 2012, 100, .	1.5	29
159	Fabrication of nano-patterns using quick gel-nanoimprint process. , 2012, , .		5
160	Crystallization to polycrystalline silicon thin film and simultaneous inactivation of electrical defects by underwater laser annealing. Applied Physics Letters, 2012, 101, 252106.	1.5	14
161	Nanodot-type floating gate memory with high-density nanodot array formed utilizing listeria ferritin. , 2012, , .		0
162	Low-temperature fabrication of solution-processed InZnO thin-film transistors with Si impurities by UV/O ₃ -assisted annealing. AIP Advances, 2012, 2, .	0.6	20

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163	Analysis of Electron Traps in a-IGZO Thin Films after High Pressure Vapor Annealing by Capacitance-Voltage Method. Materials Research Society Symposia Proceedings, 2012, 1436, 1.	0.1	1
164	Construction of Au nanoparticle/ferritin satellite nanostructure. Chemical Physics Letters, 2012, 547, 52-57.	1.2	2
165	Highly reliable a-InGaZnO thin film transistors with new SiN _x gate insulators. , 2012, , .		0
166	Effect of high-pressure deuterium oxide annealing on Al ₂ O ₃ deposited by plasma-assisted atomic layer deposition at low temperature. , 2012, , .		0
167	Dependence of semiconductor nanoparticle size on spray condition in electro-spray deposition method. , 2012, , .		1
168	Nanodot-type floating gate memory with high-density nanodot array formed utilizing Listeria Dps. , 2012, , .		0
169	Analysis of electron traps in SiO ₂ /IGZO interface by cyclic capacitance-voltage method. , 2012, , .		2
170	Metal-nanoparticle-induced crystallization of amorphous Ge film using ferritin. Applied Surface Science, 2012, 258, 3410-3414.	3.1	13
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